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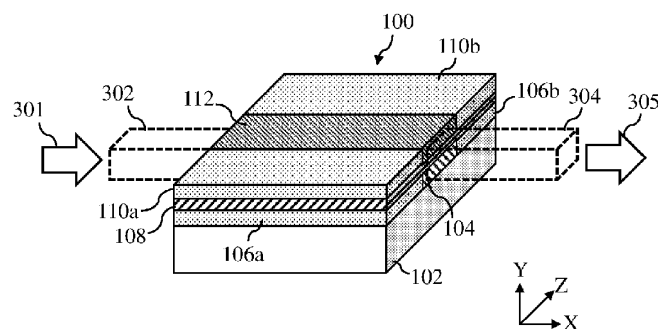


FIGURE 3

(57) Abstract: This document describes a slot waveguide modulator that utilizes both silicon photonics and electro-optic materials to achieve high bandwidth, high efficiency and low optical loss. The slot waveguide modulator has an electro-optic layer that is sandwiched between two mode stopper layers, where the mode stopper layers are formed in waveguide layers having a refractive index that is higher than the refractive index of the electro-optic layer.